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### **Supporting Information**

# **Enhancing High-Performance Supercapattery Electrodes: Harnessing**

### **Structural and Compositional Synergies via Phosphorus Doping on Bimetallic**

## **Boride for Rapid Charging**

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### **Characterizations**

23 X-ray diffraction (XRD) analysis was conducted using a Rigaku X-ray diffractometer with CuK $\alpha$  radiation. The morphology and microstructure of the samples were examined using high-resolution scanning electron microscopy (HR-SEM; JEOL JSM-7500F) and transmission electron microscopy (TEM; TECNAI G2 F20 TEM system). X-ray photoelectron spectroscopy (XPS) was employed using an ESCALAB-MKII system (VG Scientific Co.). XPS had an Al K alpha source, and the results had been characterized by the Fityk software. Gaussian as a fitting function was used to characterize the XPS results. Brunauer-Emmett-Teller (BET, ASAP2010, Micromeritics) analysis was used to determine the surface area of the prepared samples.

#### **Supercapattery measurements**

 The electrochemical capacitive properties of the as-synthesized nanostructure electrodes were investigated in an aqueous 2 M KOH solution using a three-electrode cell. The as-fabricated materials on Ni foam, platinum (Pt) foil and standard calomel electrode (SCE) were employed as the working, counter, and reference electrodes, respectively. The mass loadings of P-NCB and R- GO were calculated to be 3.5 mg cm-2 and 2 mg cm-2 respectively. In the supercapattery cell, the P-NCB electrode was used as the positrode and R-GO as the negatrode with 2M KOH/PVA gel employed as the electrolyte.

39 The specific capacitance  $(C_s, F g^{-1})$  and specific capacity  $(C_m, C g^{-1})$  were calculated from 40 galvanostatic charge/discharge (GCD) testing using the Eq.  $(1)$  and  $(2)$ , respectively<sup>1</sup>:

$$
= \frac{2i/V dt}{m (V_f - V_i)^2}
$$
 (1)

$$
C_{\rm m} = C_s \times \Delta V \tag{2}
$$

44 where, m (g), i (A), (V<sub>f</sub>-V<sub>i</sub>), and <sup>f dt</sup> are the mass of the active materials coated on the Ni foam, the applied current, the functional potential frame, and the integral area of the discharge curve, respectively.

 The energy density (E) and power density (P) of the supercapattery were calculated according to Eq. (3) and (4), respectively:

$$
E = \frac{I \int V dt}{3.6} \tag{3}
$$

$$
P = \frac{3600 \times E}{t} \tag{4}
$$

51 where I (A  $g^{-1}$ ) and t (s) are the current density, and discharge time of the supercapattery cell, respectively.

## **Supercapattery device fabrication**

 The solid-state supercapattery device was assembled by using optimized P-NCB as the positrode and R-GO as the negatrode with cellulose paper as a separator, respectively. A PVA–KOH gel electrolyte was used as the conducting medium in the assembled two-electrode device system. The gel electrolyte was prepared by taking about 10 gm PVA in 80 mL deionized water and kept at 160 °C for about 4 h for complete dissolution. Separately, 2M KOH solution was prepared in 20 mL deionized water and added to the above solution to form a PVA–KOH gel electrolyte with required consistency. Both the negatrode and positrodes were soaked in the electrolyte along with the cellulose paper for about 5 min. After proper soaking, the device was assembled and allowed  to dry under the air atmosphere for about 24 h to obtain a completely solidified device. The dried solid-state supercapattery device was subjected to cyclic voltammetry and galvanostatic charge– discharge analysis. The cyclic stability of the fabricated asymmetric supercapacitor device has been recorded using an automatic battery cycler (WBCS3000)<sup>2</sup> .



 **Fig. S1.** SEM images of the nanostructure of the (a, b) NC, (c, d) NCB, (e, f) P-NC and (g, h) P-NCB samples.



 **Fig. S2.** N<sup>2</sup> adsorption–desorption isotherms for (a) NC, (b) NCB, (c) P-NC and (d) P-NCB samples. The inset shows the corresponding pore size distribution profiles.



 **Fig. S3.** SEM images of the nanostructure of the (a, b) P-NCB-70-350°, (c, d) P-NCB-210-350°, (e, f) P-NCB-140-300° and (g, h) P-NCB-140-400° samples.





 **Fig. S4.** CV profile at different scan rate and GCD profile at different current density of (a, b) NC, (c, d) NCB and (e, f) P-NC samples respectively.



 **Fig. S5.** R-GO characterizations (a) XRD spectra, (b) Raman Spectra, (c) CV profile at different scan rate, (d) GCD profile at different current density.





 **Fig. S6.** XPS spectra of post 50,000 cycles of GCD stability of P-NCB sample (a) Ni 2p, (b) Co 2p, (c) B 1s and (d) P 2p.



**Fig. S7.** SEM images of (a, b) P-NCB and (c, d) post 50,000 cycles of GCD stability sample e)

88 XPS spectra of O 1s to indicate the  $O_v$  before and after 50,000 cycles stability.



 **Fig. S8.** EDAX analysis on elemental composition of P-NCB (a) before stability and (b) after 50,000 cycles of GCD stability sample.



94

95 **Fig. S9.** XRD images of P-NCB pre and post 50,000 cycles of GCD stability sample

### 96 **Trasatti Method**

97 The contributions of the pseudocapacitive and electrical double layer mechanisms are typically 98 calculated using the Trasatti method<sup>3, 4</sup>. First, the areas of the CV curves at various scan rates are 99 evaluated and the capacitance is calculated using the following formula:

$$
C = \frac{A}{2 \Delta V v}
$$

 $\boldsymbol{A}$ 

101 where *C* is the areal capacitance (mF/cm<sup>2</sup>),  $\Delta V$  refers to the potential window (V), and *A* is the area 102 enclosed by the CV curves (mAV/cm<sup>2</sup> ) at different scan rates *v* (V/s). Assuming a semi-infinite 103 diffusion pattern of ion diffusion, a linear relationship can be derived between the reciprocal of 104 areal capacitance  $(I/C)$  and square root of scan rates  $(v^{1/2})$  as follows:

$$
\frac{1}{105} \frac{1}{C} = \frac{1}{C_T} + cv^{1/2}
$$

106 where  $C_T$  is the maximum capacitance (mF/cm<sup>2</sup>), the sum of the contributions of the 107 pseudocapacitive and electrical double layer mechanisms, and *c* is a constant. The electrical double 108 layer contribution can be calculated using the following relation,

$$
C = C_{EDLC} + cv^{-1/2}
$$

110 The intercept obtained from linear fitting of the above relationship gives the value of the 111 electrical double layer contribution at the maximum areal capacitance. The subtraction of *CEDLC* 112 from  $C_T$  yields the maximum pseudocapacitance  $(C_D)$ .

$$
C_D = C_T - C_{EDLC}
$$

114 The power-law equation was employed

$$
i = av^b
$$

$$
log i = log a + b log v
$$

117 where i is the redox peak current  $(mA)$ , v is the scan rate  $(mV/s)$ , and a and b are constants<sup>5</sup>.



 **Fig. S10**. (a, b, c) Plots of reciprocal of areal capacitance (1*/C*) versus square root of scan rates (*v*  $(v^{1/2})$  and (d, e, f) plots of gravimetric capacitance (C) versus reciprocal of square root of scan rate (*v*  $(v<sup>1/2</sup>)$  and (g, h, i) Calculated contribution of diffusion controlled charge storage mechanism of the P-NCB, R-GO and device P-NCB//R-GO respectively.

## **Calculation of Surface-Active Sites**

124 Associated charge with the reduction peak  $(Q)$  can be calculated using the following expression<sup>6</sup>:

$$
Q = \frac{\int I \, dV}{v}
$$

126 where *Q* (C) is the total charge associated with the reduction peak and *v* (V/s) is the scan rate. For 127 simplicity, we assume that all the surface redox reactions are single electron transfer reactions. 128 Then, the number of electrons calculated above is the number of surface-active sites  $(N)$ .  $q = 1.602$ 129  $\times$  10<sup>-19</sup> C.

$$
N = \frac{Q}{q}
$$



 **Fig. S11.** CV profile of non-faradaic regions of (a) NC, (b) NCB, (c) P-NC, (d) P-NCB 133 respectively, (e) ECSA calculation derived from C<sub>dl</sub>, and (f) Nyquist plots for the as-prepared 134 samples at 0.4 V<sub>SCE</sub> and the image shows the electrochemical equivalent circuit (inset: magnified image of Nquist plot).

136 **Table S1.** A comparison between the solution resistance (Rs) and charge transfer resistance (Rct) of 137 the samples after fitting the EIS data.



138

139 **Table S2.** Comparison of the electrochemical performance in 2 M KOH solution of the P-NCB in

140 three electrode setup with reported electrocatalysts.





142 **Table S3.** Comparison of the electrochemical performance of device prepared using P-NCB// R-GO

143 with reported other device setups.





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